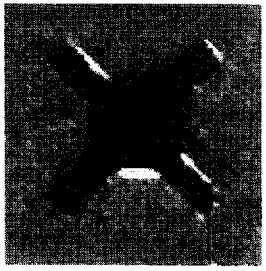
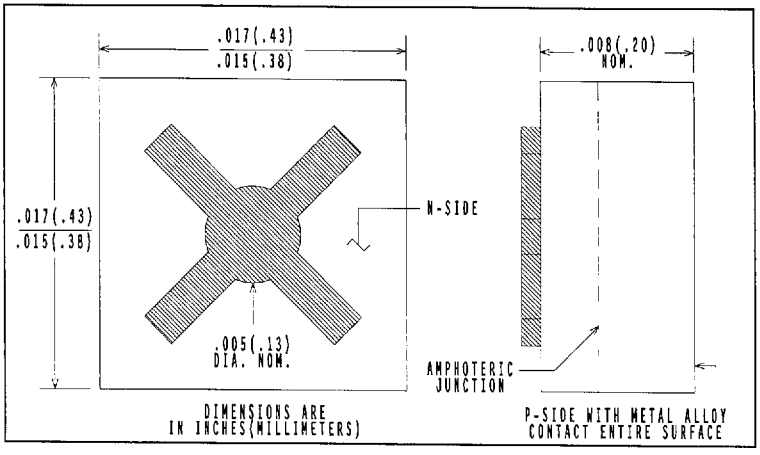
GaAlAs Infrared Emitter Chip
Type OPC216





Features

- High infrared radiation output
- Low degradation
- Microalloyed gold contacts

Description

Infrared emitting diode chips are fabricated by solution epitaxial techniques which provide high efficiency, long operating life, and minimum degradation. Spectral emission is centered at 890 nanometers.

Optek chip warranty excludes any damage resulting from improper bonding or alloying techniques.

Packaging Options

OPC216VP	Vials
OPC216TP	Sawn on Tape
OPC216WP	Waffle Pack

Absolute Maximum Ratings[1] (T_A = 25° C unless otherwise noted)

Storage and Operating Temperature	-55° C to +150° C
Forward DC Current	150 mA[2]
Peak Forward Current (1 µs pulse width, 300 pps)	3.0 A
Power Dissipation	200 mW

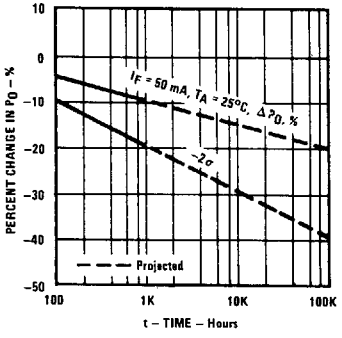
Electrical Characteristics (T_A = 25° C unless otherwise noted)

SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS
V_R	Reverse Voltage	2.0			V	I_R = 10 µA
V_F	Forward Voltage			1.95	V	I_F = 100 mA
P_O	Radiant Power Output	4.0	7.5		mW	I_F = 100 mA[3]

Notes: (1) All maximum ratings are determined with the chip mounted on a dimpled TO-46 header using Optek techniques. (2) Maximum operating current is a function of the package in which the chip is housed and the environment in which the assembled package will be used. (3) Typical wavelength at peak emission is 890 nm.

Typical Performance Curves

Percent Change in Power Output vs Time



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